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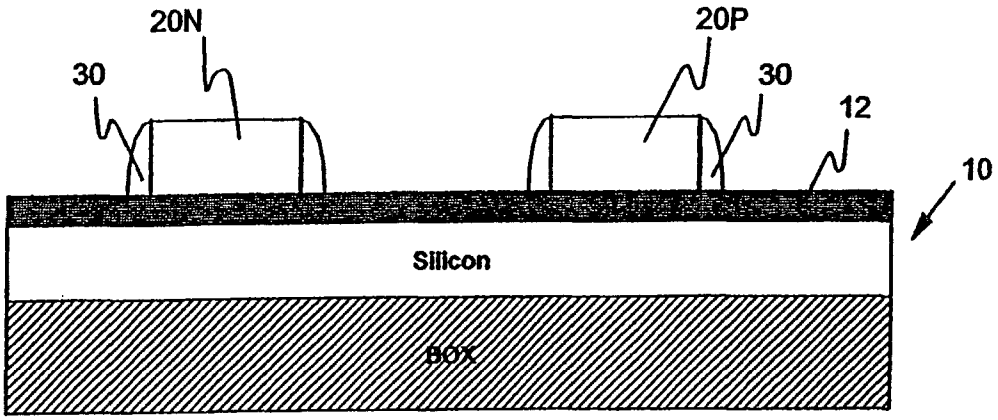
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(54) Title: DENSE DUAL-PLANE DEVICES



(57) Abstract: An MOS device with first and second freestanding semiconductor bodies (40N, 40P) formed on a substrate (10). The first freestanding semiconductor body (40N or 40P) has a first portion thereof disposed at a non-orthogonal, non parallel orientation with respect to a first portion of the second freestanding semiconductor body (40P or 40N). These portions of said first and second freestanding semiconductor bodies (40N, 40P) have respective first and second crystalline orientations. A first gate electrode (60) crosses over at least part of said first portion of said first freestanding semiconductor body (40N or 40P) at a non-orthogonal angle, as does a second gate electrode (60) over the first portion of the second freestanding semiconductor body (40P or 40N).

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